

**METHOD AND STRUCTURE FOR FABRICATING PATTERNS ON  
PHASE SHIFT MASK FOR THE MANUFACTURE OF  
SEMICONDUCTOR WAFERS**

**ABSTRACT OF THE DISCLOSURE**

A reticle structure for integrated circuit device. The structure includes a transparent substrate having a surface region and a plurality of spaced regions on the surface region. Each of the spaced regions is configured to form an array, which has a plurality of rows that intersect a plurality of columns. Each of the spaced regions is defined within a pair of rows and a pair of columns; whereupon each of the spaced regions being separated by each other by a common dimension of no greater than 0.25 microns. At least one of the spaced regions includes a code to define a masked read only memory (ROM) structure. The one coded spaced region causes an interference with a light source to transmit a lower intensity of light relative to any one of the spaced regions free from the coding.

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